

GTS9926**N-CHANNEL ENHANCEMENT MODE POWER MOSFET**

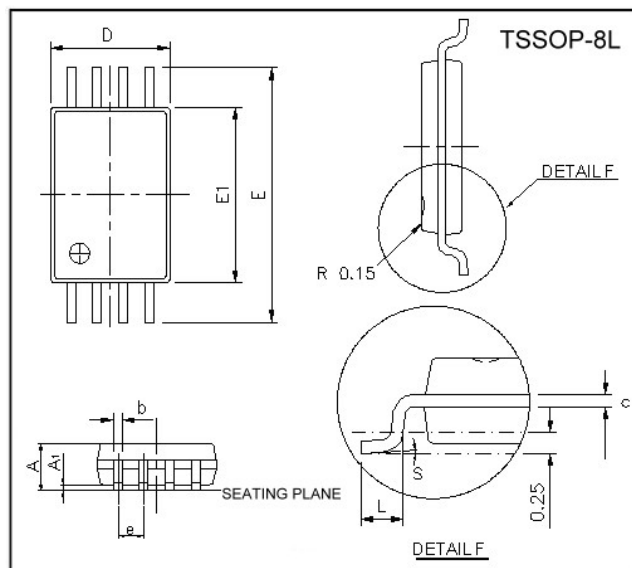
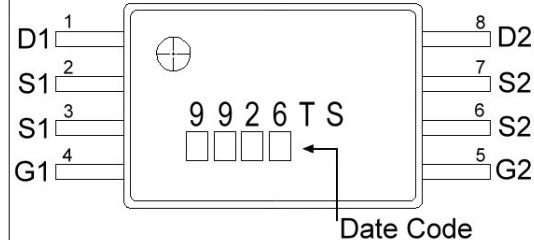
BVD _{SS}	20V
R _{DS(ON)}	28mΩ
I _D	6A

Description

The GTS9926 provides the designer with the best combination of fast switching, ruggedized device design, ultra low on-resistance and cost-effectiveness.

Features

- *Low on-resistance
- *Capable of 2.5V gate drive
- *Low drive current

Package Dimensions**Marking :**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	-	1.20	E	6.20	6.60
A1	0.05	0.15	E1	4.30	4.50
b	0.19	0.30	e	0.65 BSC	
c	0.09	0.20	L	0.45	0.75
D	2.90	3.10	S	0°	8°

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±12	V
Drain Current ³ , V _{GS} @4.5V	I _D @Ta=25°C	6	A
Drain Current ³ , V _{GS} @4.5V	I _D @Ta=70°C	4.8	A
Pulsed Drain Current ¹	I _{DM}	20	A
Power Dissipation	P _D @Ta=25°C	1	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 ~ +150	°C
Linear Derating Factor		0.008	W/°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-ambient ³ Max.	R _{thj-a}	125	°C/W

Electrical Characteristics (T_j = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} =0, I _D =250uA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} / ΔT _j	-	0.03	-	V/°C	Reference to 25°C, I _D =1mA
Gate Threshold Voltage	V _{GS(th)}	0.5	-	1.2	V	V _{DS} =V _{GS} , I _D =250uA
Forward Transconductance	g _{fs}	-	20	-	S	V _{DS} =10V, I _D =6A
Gate-Source Leakage Current	I _{GSS}	-	-	±100	nA	V _{GS} = ±12V
Drain-Source Leakage Current(T _j =25°C)	I _{DSS}	-	-	1	uA	V _{DS} =20V, V _{GS} =0
Drain-Source Leakage Current(T _j =70°C)		-	-	25	uA	V _{DS} =16V, V _{GS} =0
Static Drain-Source On-Resistance ²	R _{DS(ON)}	-	-	28	mΩ	V _{GS} =4.5V, I _D =6.0A
		-	-	38		V _{GS} =2.5V, I _D =5.2A
Total Gate Charge ²	Q _g	-	23	-	nC	I _D =6A V _{DS} =20V V _{GS} =5.0V
Gate-Source Charge	Q _{gs}	-	4.5	-		
Gate-Drain ("Miller") Change	Q _{gd}	-	7	-		
Turn-on Delay Time ²	T _{d(on)}	-	30	-	ns	V _{DS} =10V I _D =1A V _{GS} =5V R _G =6Ω R _D =10Ω
Rise Time	T _r	-	70	-		
Turn-off Delay Time	T _{d(off)}	-	40	-		
Fall Time	T _f	-	65	-		
Input Capacitance	C _{iss}	-	1035	-	pF	V _{GS} =0V V _{DS} =20V f=1.0MHz
Output Capacitance	C _{oss}	-	320	-		
Reverse Transfer Capacitance	C _{rss}	-	150	-		

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V _{SD}	-	-	1.2	V	I _S =1.7A, V _{GS} =0, T _j =25°C
Continuous Source Current(Body Diode)	I _S	-	-	1.54	A	V _D = V _G =0V, V _S =1.3V

Notes: 1. Pulse width limited by Max. junction temperature.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

3. Surface mounted on 1 in² copper pad of FR4 board; 208°C/W when mounted on Min. copper pad.

Characteristics Curve

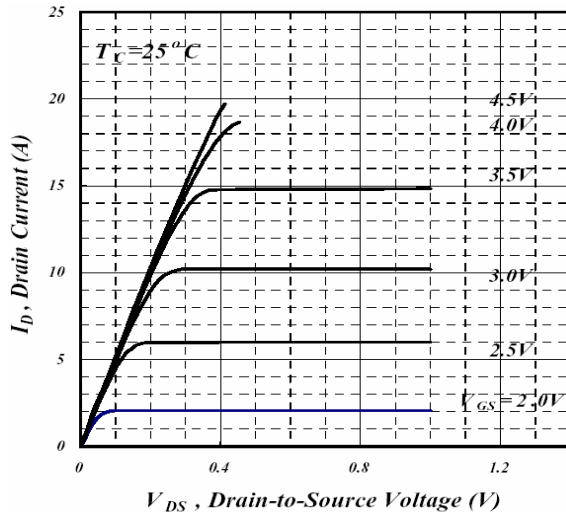


Fig 1. Typical Output Characteristics

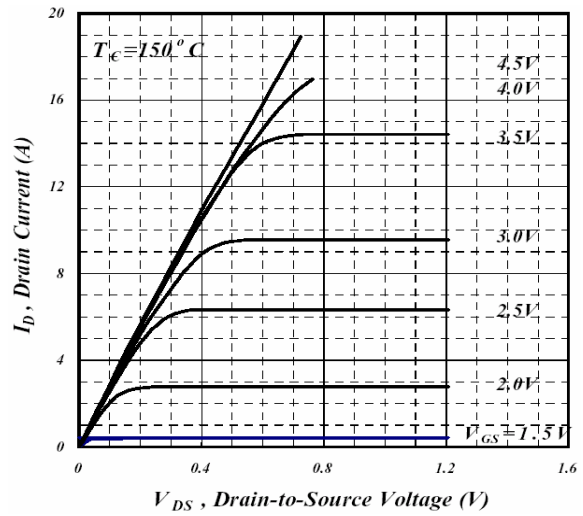


Fig 2. Typical Output Characteristics

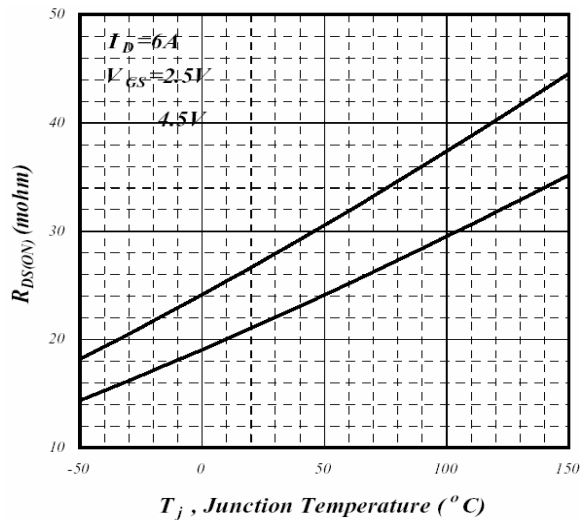


Fig 3. $R_{DS(ON)}$ v.s. Junction Temperature

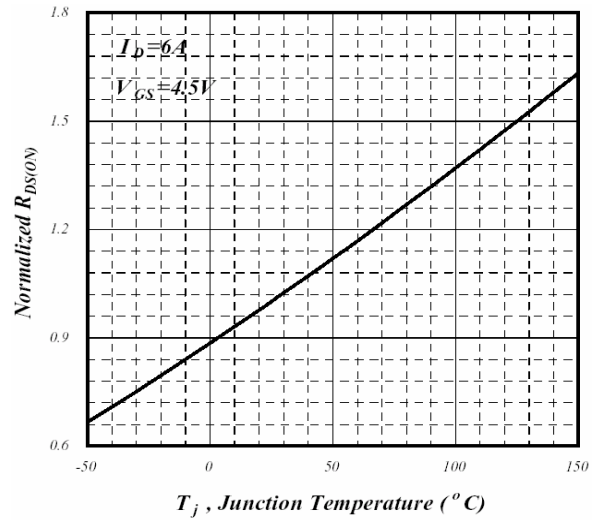


Fig 4. Normalized On-Resistance v.s. Junction Temperature

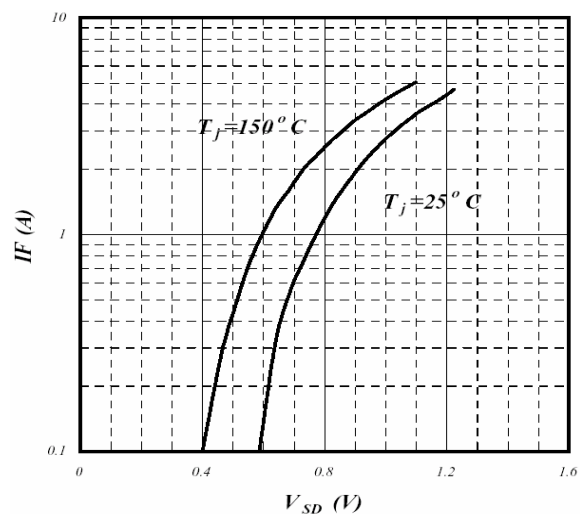


Fig 5. Forward Characteristics of Reverse Diode

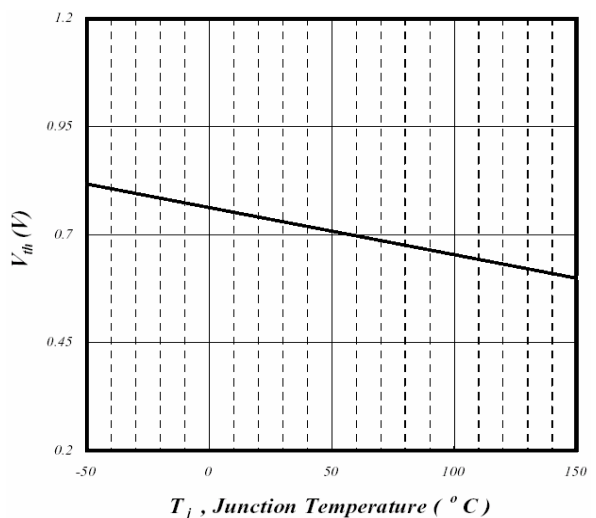


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

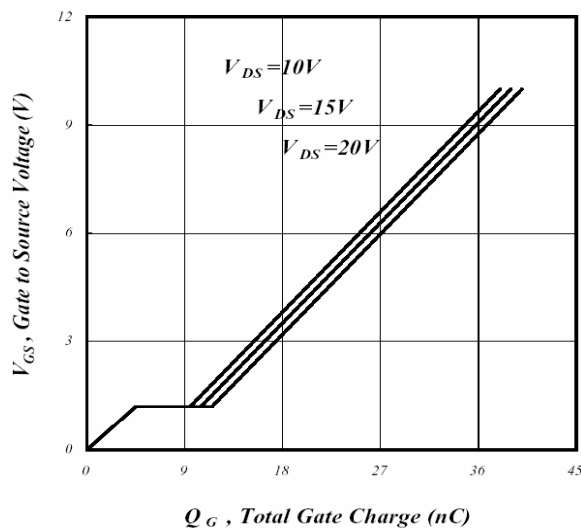


Fig 7. Gate Charge Characteristics

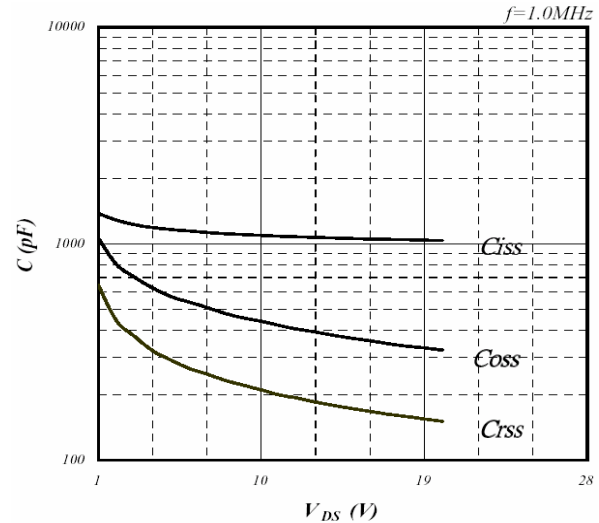


Fig 8. Typical Capacitance Characteristics

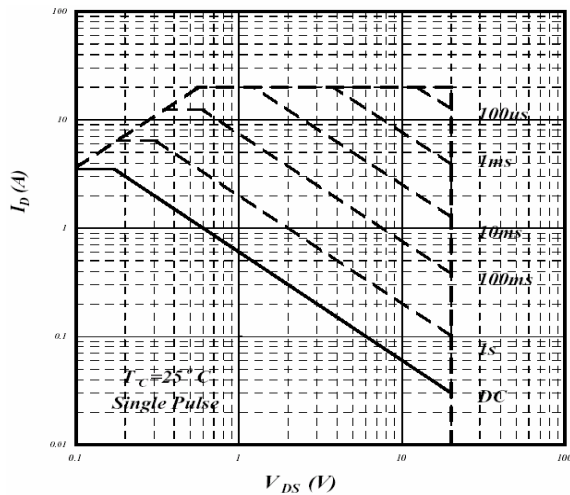


Fig 9. Maximum Safe Operating Area

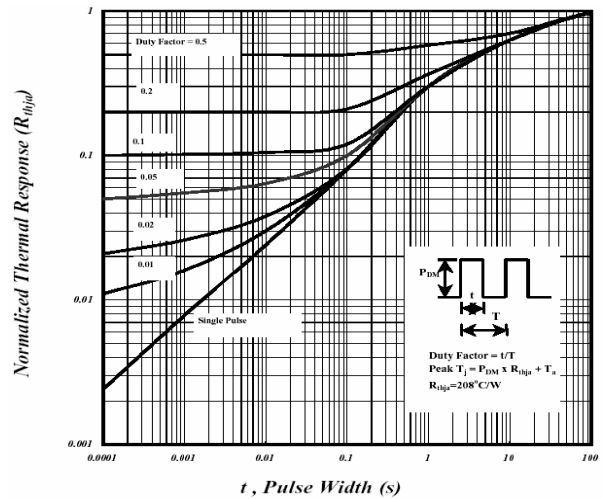


Fig 10. Effective Transient Thermal Impedance

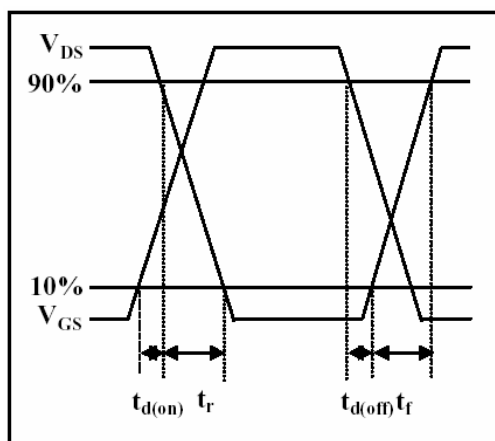


Fig 11. Switching Time Waveform

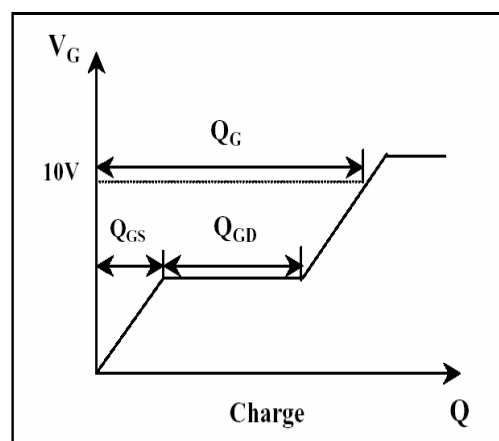


Fig 12. Gate Charge Waveform

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